

# NTLUS3A39PZ

## MOSFET – Power, Single, P-Channel, ESD, UDFN, 1.6x1.6x0.55 mm -20 V, -5.2 A



ON Semiconductor®

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### Features

- UDFN Package with Exposed Drain Pads for Excellent Thermal Conduction
- Low Profile UDFN 1.6 x 1.6 x 0.55 mm for Board Space Saving
- Ultra Low  $R_{DS(on)}$
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### Applications

- Optimized for Power Management Applications for Portable Products, Such as Cell Phones, PMP, Media Tablets, DSC, GPS, and Others
- Battery Switch
- High Side Load Switch

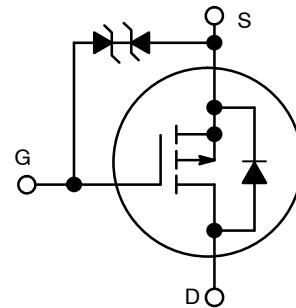
### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter		Symbol	Value	Unit	
Drain-to-Source Voltage		$V_{DSS}$	-20	V	
Gate-to-Source Voltage		$V_{GS}$	$\pm 8.0$	V	
Continuous Drain Current (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	$I_D$	-5.2	A
				$T_A = 85^\circ\text{C}$	
	$t \leq 5$ s	$T_A = 25^\circ\text{C}$	-6.4		
Power Dissipation (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	$P_D$	1.5	W
				$t \leq 5$ s	
Continuous Drain Current (Note 2)	Steady State	$T_A = 25^\circ\text{C}$	$I_D$	-3.4	A
				$T_A = 85^\circ\text{C}$	
Power Dissipation (Note 2)		$T_A = 25^\circ\text{C}$	$P_D$	0.6	W
Pulsed Drain Current		$t_p = 10 \mu\text{s}$	$I_{DM}$	-17	A
Operating Junction and Storage Temperature		$T_J, T_{STG}$	-55 to 150	$^\circ\text{C}$	
Source Current (Body Diode) (Note 2)		$I_S$	-1	A	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		$T_L$	260	$^\circ\text{C}$	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

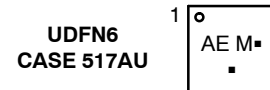
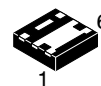
1. Surface Mounted on FR4 Board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces).
2. Surface-mounted on FR4 board using the minimum recommended pad size of 30 mm<sup>2</sup>, 2 oz. Cu.

MOSFET		
$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	$I_D$ MAX
-20 V	39 m $\Omega$ @ -4.5 V	-5.2 A
	50 m $\Omega$ @ -2.5 V	
	81 m $\Omega$ @ -1.8 V	
	147 m $\Omega$ @ -1.5 V	



P-Channel MOSFET

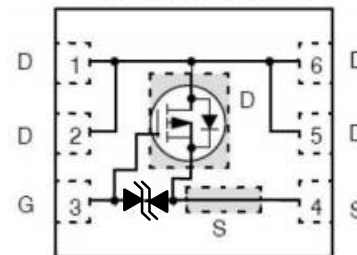
### MARKING DIAGRAM



AE = Specific Device Code  
M = Date Code  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

### PIN CONNECTIONS



(Top View)

### ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

# NTLUS3A39PZ

## THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Ambient – Steady State (Note 3)	$R_{\theta JA}$	85	°C/W
Junction-to-Ambient – $t \leq 5$ s (Note 3)	$R_{\theta JA}$	55	
Junction-to-Ambient – Steady State min Pad (Note 4)	$R_{\theta JA}$	200	

3. Surface-mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces).  
 4. Surface-mounted on FR4 board using the minimum recommended pad size of 30 mm<sup>2</sup>, 2 oz. Cu.

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
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### OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0$ V, $I_D = -250$ $\mu$ A	-20			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	$I_D = -250$ $\mu$ A, ref to $25^\circ\text{C}$		13		mV/°C
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{GS} = 0$ V, $V_{DS} = -20$ V			-1.0	$\mu$ A
Gate-to-Source Leakage Current	$I_{GSS}$	$V_{DS} = 0$ V, $V_{GS} = \pm 8.0$ V			$\pm 10$	$\mu$ A

### ON CHARACTERISTICS (Note 5)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}$ , $I_D = -250$ $\mu$ A	-0.4		-1.0	V
Negative Threshold Temp. Coefficient	$V_{GS(TH)}/T_J$			3.0		mV/°C
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = -4.5$ V, $I_D = -4.0$ A		30	39	m $\Omega$
		$V_{GS} = -2.5$ V, $I_D = -2.0$ A		40	50	
		$V_{GS} = -1.8$ V, $I_D = -1.2$ A		55	81	
		$V_{GS} = -1.5$ V, $I_D = -0.5$ A		75	147	
Forward Transconductance	$g_{FS}$	$V_{DS} = -5$ V, $I_D = -3.0$ A		25		S

### CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	$C_{ISS}$	$V_{GS} = 0$ V, $f = 1$ MHz, $V_{DS} = -15$ V		920		pF
Output Capacitance	$C_{OSS}$			85		
Reverse Transfer Capacitance	$C_{RSS}$			80		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = -4.5$ V, $V_{DS} = -15$ V; $I_D = -3.0$ A		10.4		nC
Threshold Gate Charge	$Q_{G(TH)}$			0.5		
Gate-to-Source Charge	$Q_{GS}$			1.2		
Gate-to-Drain Charge	$Q_{GD}$			3.0		

### SWITCHING CHARACTERISTICS, $V_{GS} = 4.5$ V (Note 6)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = -4.5$ V, $V_{DD} = -15$ V, $I_D = -3.0$ A, $R_G = 1$ $\Omega$		7.2		ns
Rise Time	$t_r$			12.2		
Turn-Off Delay Time	$t_{d(OFF)}$			34.7		
Fall Time	$t_f$			34.8		

### DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	$V_{SD}$	$V_{GS} = 0$ V, $I_S = -1.0$ A	$T_J = 25^\circ\text{C}$	0.67	1.0	V
			$T_J = 125^\circ\text{C}$	0.56		
Reverse Recovery Time	$t_{RR}$	$V_{GS} = 0$ V, $dis/dt = 100$ A/ $\mu$ s, $I_S = -1.0$ A		11.1		ns
Charge Time	$t_a$			5.8		
Discharge Time	$t_b$			5.3		
Reverse Recovery Charge	$Q_{RR}$			4		nC

5. Pulse Test: pulse width  $\leq 300$   $\mu$ s, duty cycle  $\leq 2\%$ .  
 6. Switching characteristics are independent of operating junction temperatures.

# NTLUS3A39PZ

## TYPICAL CHARACTERISTICS

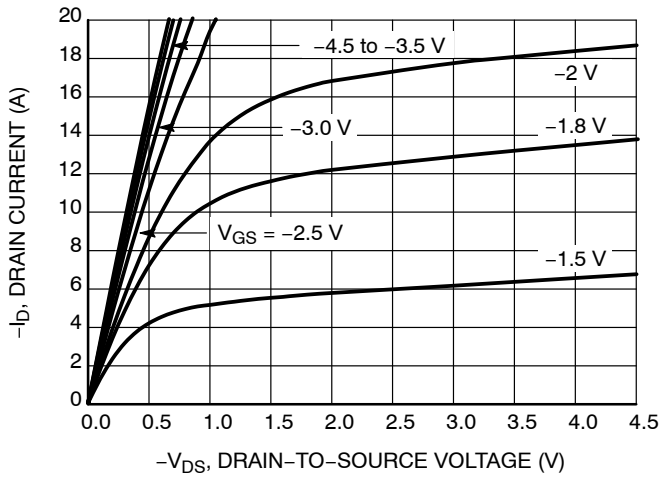


Figure 1. On-Region Characteristics

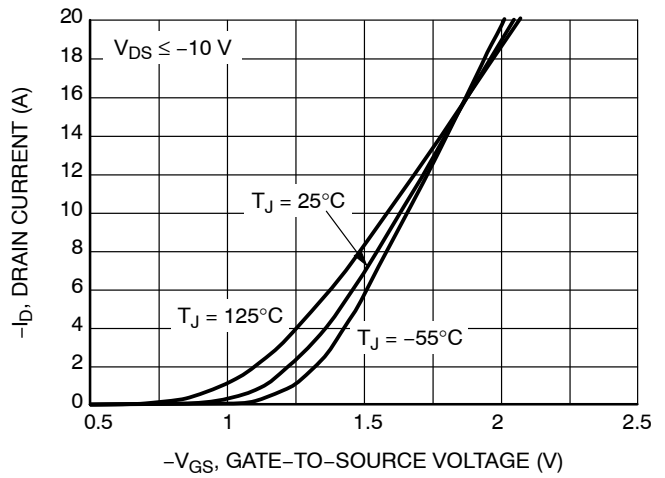


Figure 2. Transfer Characteristics

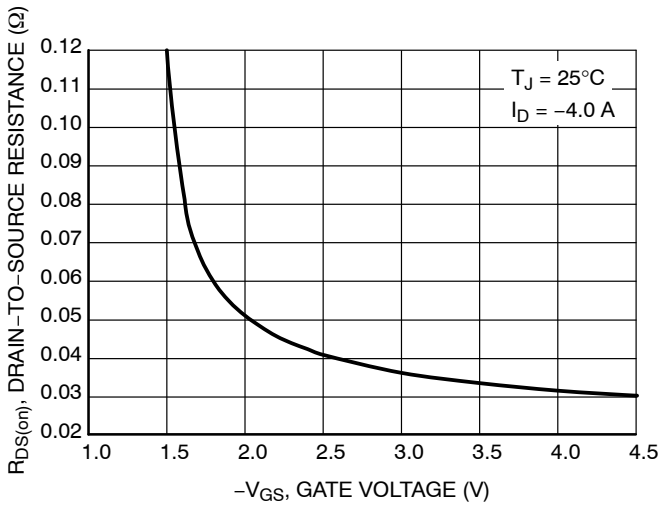


Figure 3. On-Resistance vs. Gate-to-Source Voltage

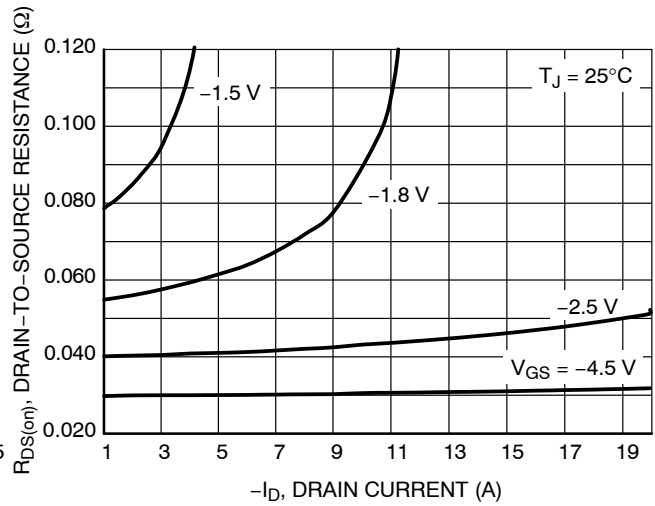


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

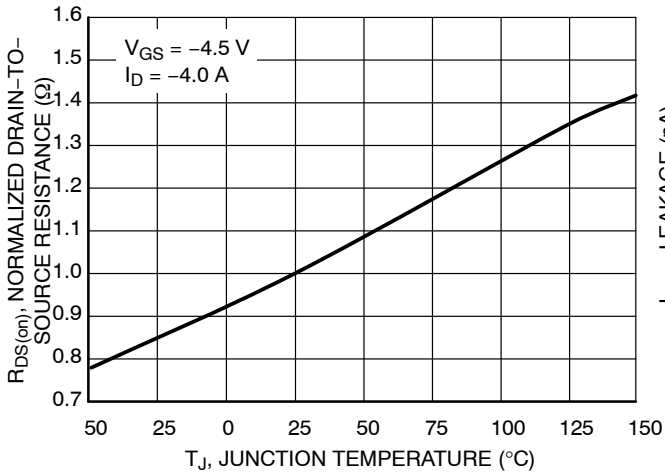


Figure 5. On-Resistance Variation with Temperature

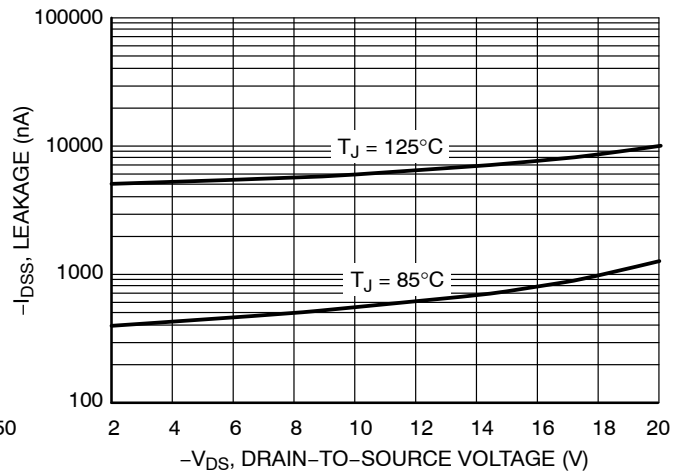


Figure 6. Drain-to-Source Leakage Current vs. Voltage

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## TYPICAL CHARACTERISTICS

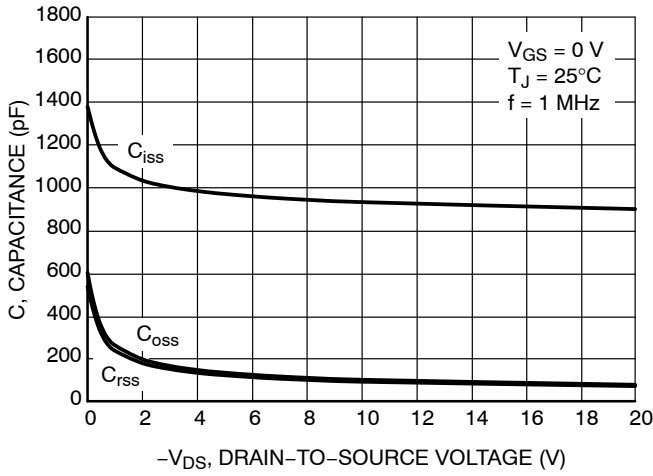


Figure 7. Capacitance Variation

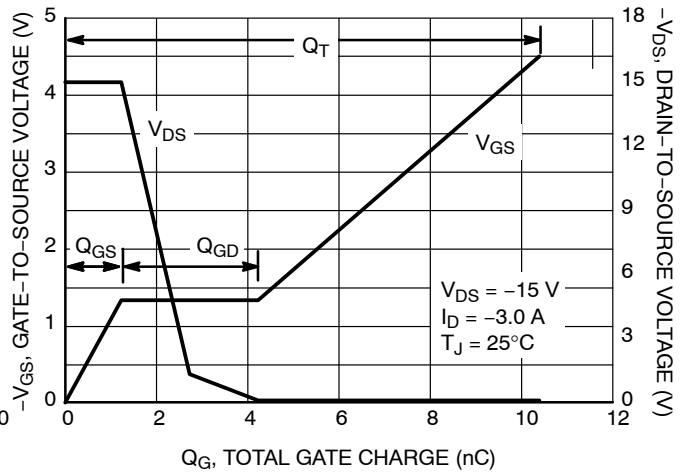


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

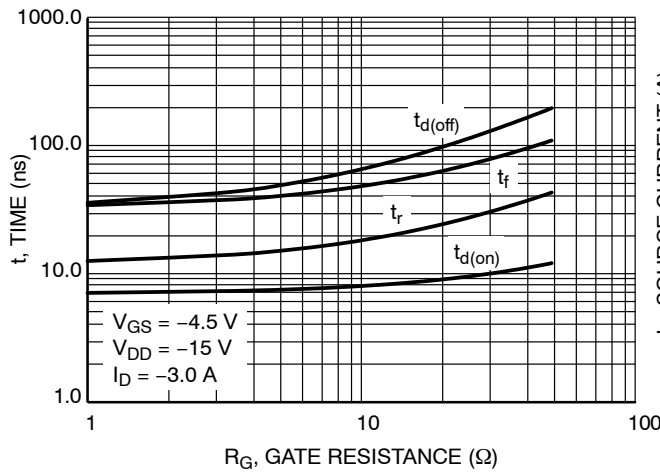


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

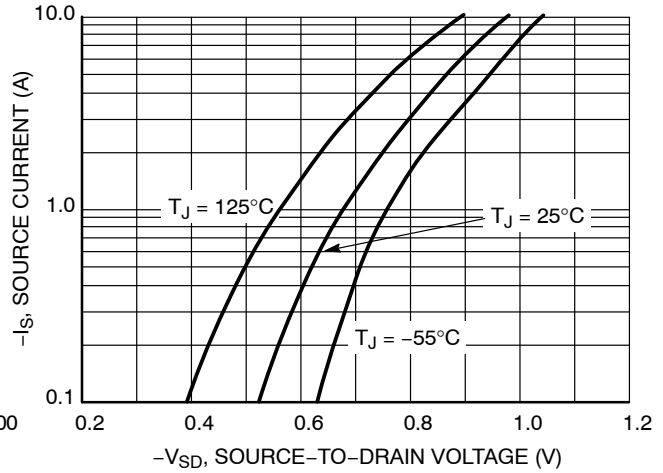


Figure 10. Diode Forward Voltage vs. Current

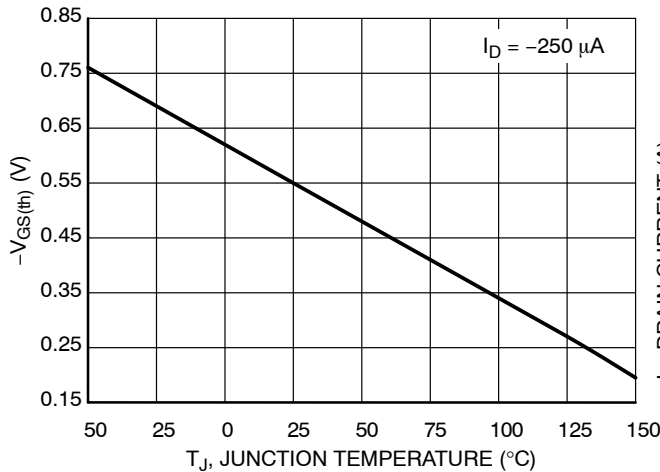


Figure 11. Threshold Voltage

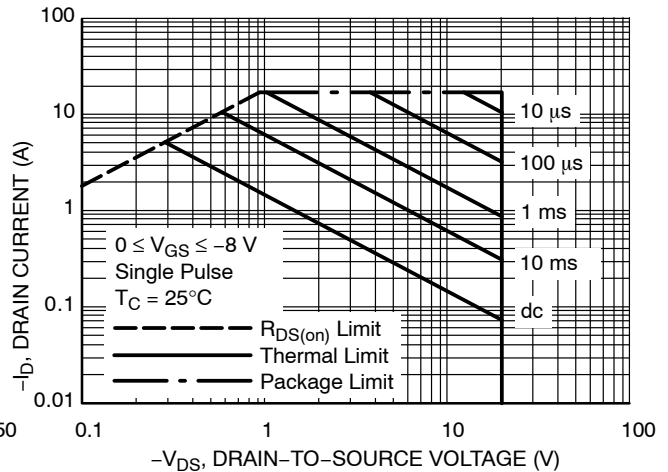


Figure 12. Maximum Rated Forward Biased Safe Operating Area

# NTLUS3A39PZ

## TYPICAL CHARACTERISTICS

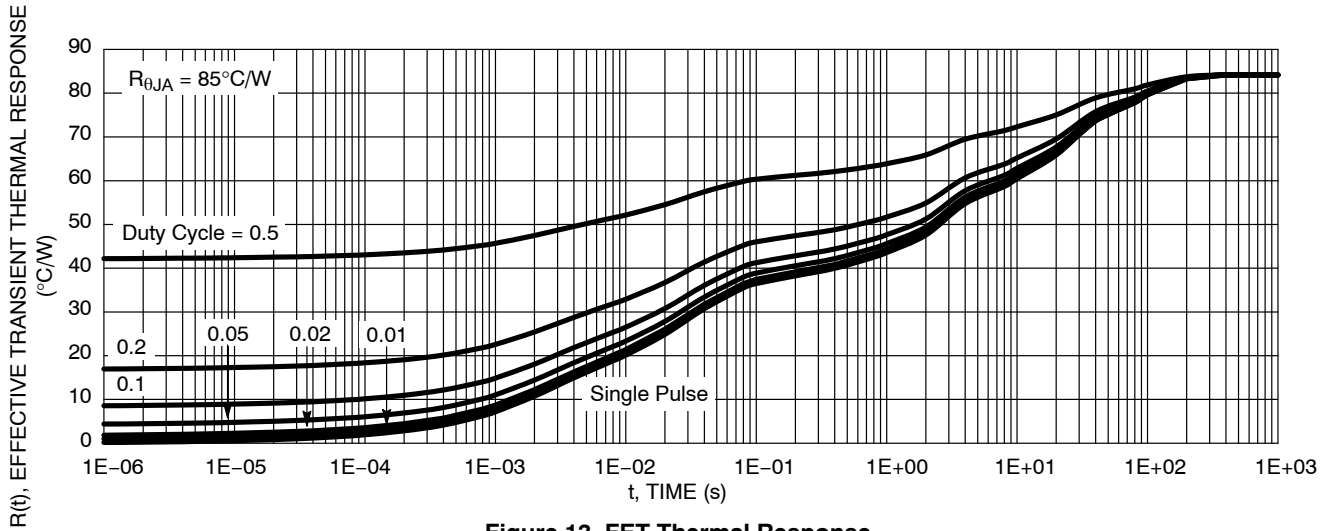


Figure 13. FET Thermal Response

### DEVICE ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
NTLUS3A39PZTAG	UDFN6 (Pb-Free)	3000 / Tape & Reel
NTLUS3A39PZTBG	UDFN6 (Pb-Free)	3000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# MECHANICAL CASE OUTLINE

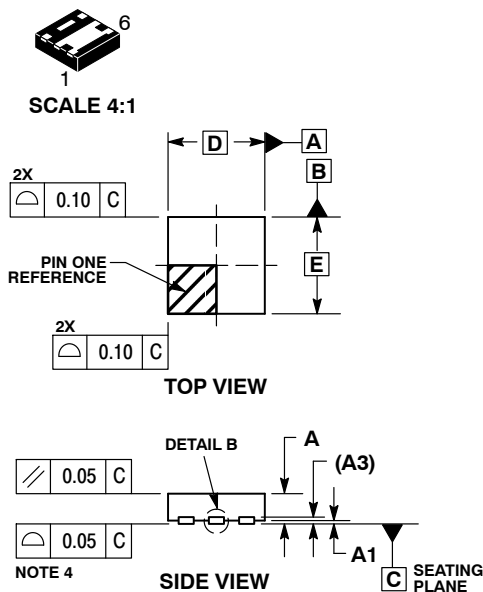
## PACKAGE DIMENSIONS

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### UDFN6 1.6x1.6, 0.5P CASE 517AU-01 ISSUE O

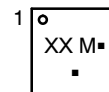
DATE 16 OCT 2008



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: MILLIMETERS.
  3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 mm FROM TERMINAL.
  4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

MILLIMETERS		
DIM	MIN	MAX
A	0.45	0.55
A1	0.00	0.05
A3	0.13	REF
b	0.20	0.30
D	1.60	BSC
E	1.60	BSC
e	0.50	BSC
D1	0.62	0.72
D2	0.15	0.25
E2	0.57	0.67
F	0.55	BSC
G	0.25	BSC
L	0.20	0.30
L1	---	0.15

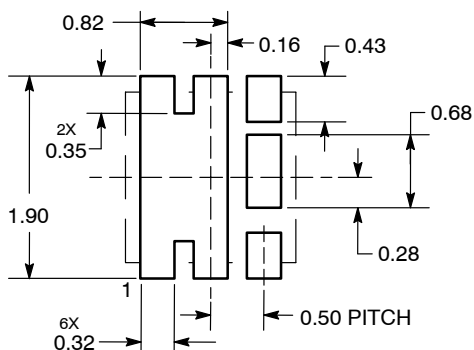
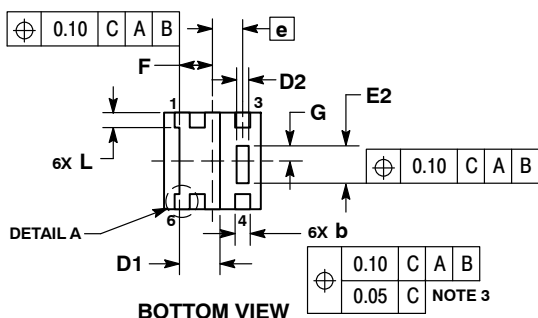
### GENERIC MARKING DIAGRAM\*



XX = Specific Device Code  
M = Date Code  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking.  
Pb-Free indicator, "G" or microdot "▪", may or may not be present.



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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<b>DESCRIPTION:</b>	<b>UDFN6, 1.6X1.6, 0.5P</b>	<b>PAGE 1 OF 1</b>

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